

Silicon NPN Power Transistors

2SD1773

DESCRIPTION

- With TO-220Fa package
- DARLINGTON
- Complement to type 2SB1193
- High speed switching

APPLICATIONS

- For medium speed switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

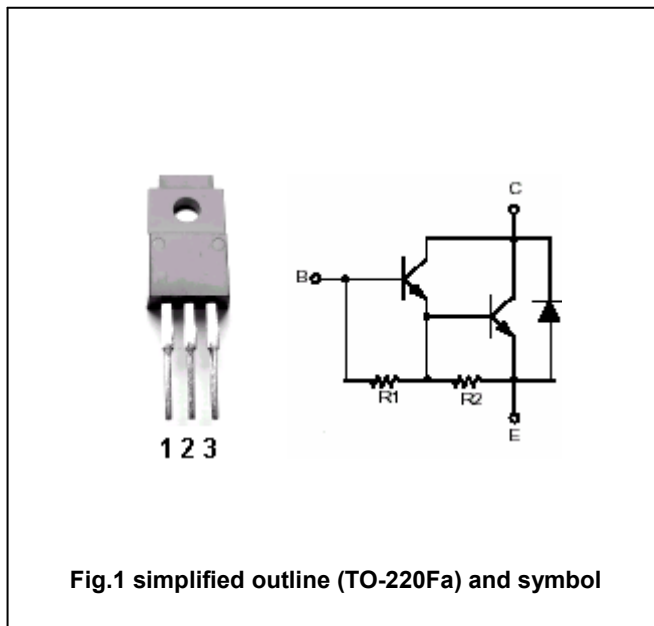


Fig.1 simplified outline (TO-220Fa) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	120	V
V _{CEO}	Collector-emitter voltage	Open base	120	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current (DC)		8	A
I _{CM}	Collector current-Peak		12	A
P _C	Collector power dissipation	T _a =25°C	2	W
		T _C =25°C	50	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =2A, L=10mH	120			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =50mA; I _C =0	7			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =4A; I _B =8mA			1.5	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =8A; I _B =80mA			3.0	V
V _{BEsat-1}	Base-emitter saturation voltage	I _C =4A; I _B =8mA			2.0	V
V _{BEsat-2}	Base-emitter saturation voltage	I _C =8A; I _B =80mA			3.5	V
I _{CBO}	Collector cut-off current	V _{CB} =120V; I _E =0			100	μA
I _{CEO}	Collector cut-off current	V _{CE} =100V; I _B =0			10	μA
h _{FE}	DC current gain	I _C =4A; V _{CE} =3V	1000		20000	
f _T	Transition frequency	I _C =0.5A; V _{CE} =10V, f=1MHz		20		MHz

Switching times

t _{on}	Turn-on time	I _C =4A; I _{B1} =8mA I _{B2} =-8mA; V _{CC} =50V		0.7		μs
t _s	Storage time			6.0		μs
t _f	Fall time			2.0		μs

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PACKAGE OUTLINE

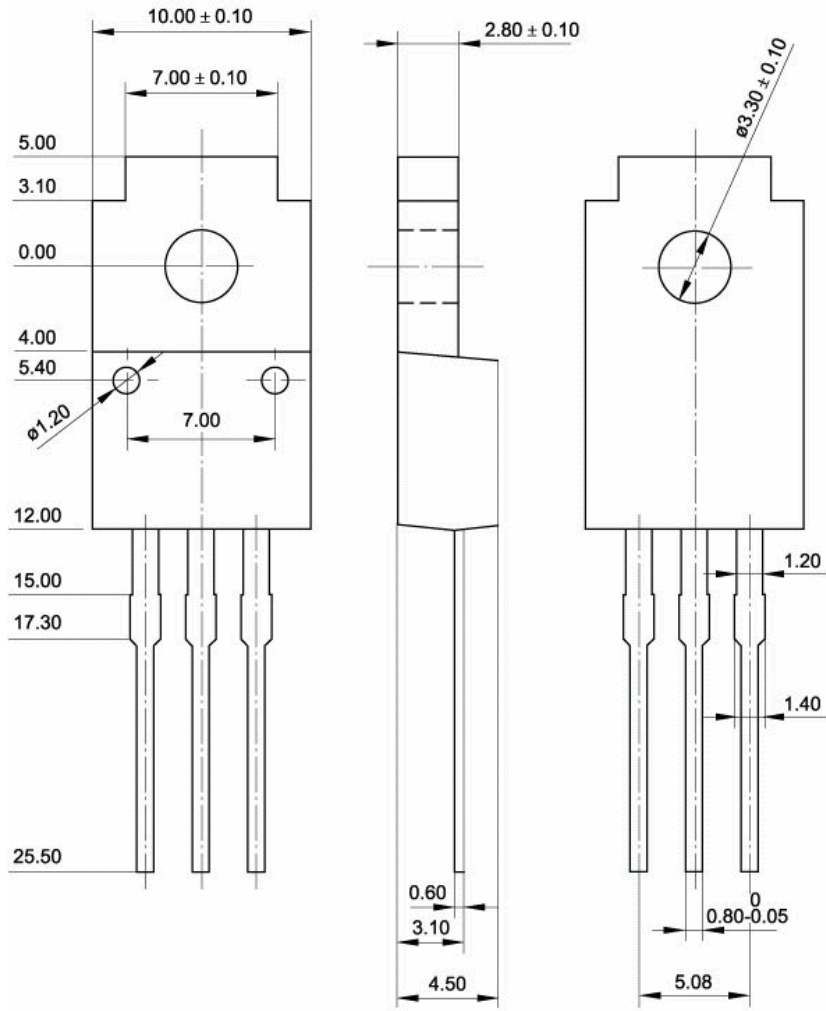


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)